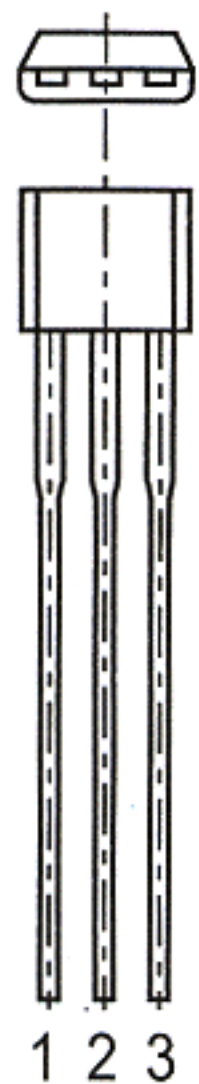


TO-92S Plastic-Encapsulate Transistors

K596 Si N-CHANNEL JUNCTION FET



TO-92S

1.SOURCE

2.GATE

3.DRAIN

FEATURES

Power dissipation

P_D : 0.1 W ($T_{amb}=25^\circ\text{C}$)

Gate current

I_G : 10 mA

Drain current

I_D : 1 mA

Drain-source voltage

BV_{GDO} : -20 V

Operating and storage junction temperature range

T_J, T_{stg} : -55°C to $+150^\circ\text{C}$

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Gate-drain breakdown voltage	BV_{GDO}	$I_G = -100 \mu\text{A}$	-20			V
Gate-source cut-off voltage	$V_{GS(off)}$	$V_{DS} = 5 \text{ V}, I_D = 1 \mu\text{A}$		-0.6	-1.5	V
Drain current	I_{DSS}	$V_{DS} = 5 \text{ V}, V_{GS} = 0$	100		800	μA
Forward transfer admittance	$ Y_{FS} $	$V_{DS} = 5 \text{ V}, V_{GS} = 0, f = 1\text{MHz}$	0.4	1.2		mS
Input capacitance	C_{iss}	$V_{DS} = 5 \text{ V}, V_{GS} = 0, f = 1\text{MHz}$		3.5		pF
Output capacitance	C_{RSS}	$V_{DS} = 5 \text{ V}, V_{GS} = 0$ $f = 1 \text{ MHz}$		0.65		pF

I_{DSS} CLASSIFICATION

Classification	A	B	C	D	E
$I_{DSS}(\mu\text{A})$	100-170	150-240	210-350	320-480	440-800